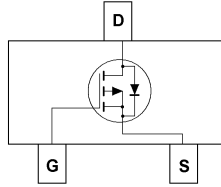


P-Channel Enhancement Mode MOSFET

$-30V_{DS} / \pm 20V_{GS} / -4.1A I_D$

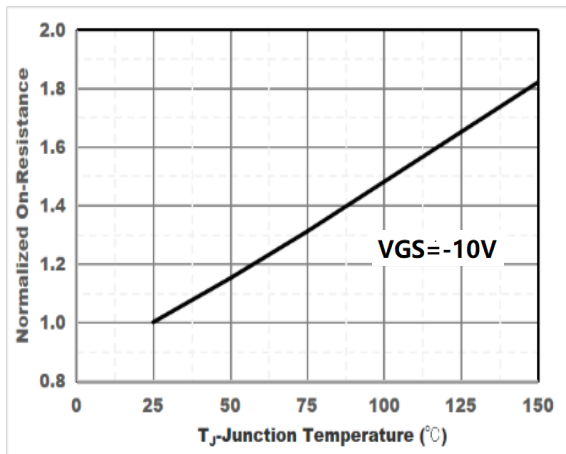


I Key Electrical Characteristics after SOT-23 package

Parameter	Description	Min.	Typ.	Max.	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30V	-33V		$V_{GS} = 0V, I_D = -250\mu A$
$I_{D(Device Ref.)}$	Continuous Drain Current			-4.1A	$T_J = 25^\circ C$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance		36 m Ω	51 m Ω	$V_{GS} = -10V, I_D = -4.1A$
			52 m Ω	68 m Ω	$V_{GS} = -4.5V, I_D = -3.5A$
$V_{GS(th)}$	Gate Threshold Voltage	-1.0V	-1.5V	-2.4 V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			-0.3 μA	$V_{DS} = -30V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-to-Source Leakage Current			$\pm 100nA$	$V_{GS} = \pm 20V$

II. Temperature vs RDS(ON) / VGS(th)

$R_{DS(ON)}$ vs Junction Temperature



$V_{GS(th)}$ vs Junction Temperature

